FMBA0656



Package: SuperSOT-6 Device Marking: **.003** Note: The " . " (dot) signifies Pin 1 Transistor 1 is NPN device, transistor 2 is PNP device.

NPN & PNP Complementary Dual Transistor SuperSOT- 6 Surface Mount Package

This device was designed for general purpose amplifier applications at collector currents to 300mA. Sourced from Process 33 (NPN) and Process 73 (PNP).

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I A = 25°C unless otherwise noted							
Symbol	Parameter	Value	Units				
V _{CEO}	Collector-Emitter Voltage	80	V				
V _{CBO}	Collector-Base Voltage	80	V				
V _{EBO}	Emitter-Base Voltage	4	V				
Ic	Collector Current (continuous)	500	mA				
PD	Power Dissipation @Ta = 25°C*	0.7	W				
T _{STG}	Storage Temperature Range	-55 to +150	°C				
TJ	Junction Temperature	150	°C				
R _{0JA}	Thermal Resistance, Junction to Ambient	180	°C/W				

*Pd total, for both transistors. For each transistor, Pd = 350 mW.

Electrical Characteristics

Absolute Maximum Ratings

 $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
BV _{CEO}	Collector to Emitter Voltage	Ic = 1.0 mA	80		V
BV _{CBO}	Collector to Base Voltage	Ic = 100 uA	80		V
BV _{EBO}	Emitter to Base Voltage	le = 100 uA	4		V

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NPN & PNP Complementary Dual Transistor

(continued)

Electrical Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Parameter	Test Conditions	Min	Мах	Units
I _{CBO}	Collector Cutoff Current	Vcb = 80 V		100	nA
I _{CEO}	Collector Cutoff Current	Vce = 60 V		100	nA
h _{FE}	DC Current Gain	Vce = 1 V, Ic = 10 mA Vce = 1 V, Ic = 100 mA	100 100		-
V _{CE(sat)}	Collector-Emitter Saturation Voltage	Ic = 100 mA, Ib = 10 mA		0.25	V
V _{BE(on)}	Base-Emitter On Voltage	Ic = 100 mA, Vce = 1 V		1.2	V

Small - Signal Characteristics

FMBA0656